



## ISO1176 Isolated RS-485 Profibus Transceiver

### 1 Features

- Meets or Exceeds the Requirements of EN 50170 and TIA/EIA-485-A
- Signaling Rates up to 40 Mbps
- Differential Output Exceeds 2.1 V (54-Ω Load)
- Low Bus Capacitance – 10 pF (Maximum)
- Up to 160 Transceivers on a Bus
- 50 kV/μs Typical Transient Immunity
- Fail-Safe Receiver for Bus Open, Short, Idle
- 3.3-V Inputs are 5-V Tolerant
- Bus-Pin ESD Protection
  - 16-kV HBM Between Bus Pins and GND2
  - 6-kV HBM Between Bus Pins and GND1
- Safety and Regulatory Approvals
  - 4000-V<sub>PK</sub> Isolation, 560-V<sub>PK</sub> V<sub>IORM</sub> per DIN V VDE V 0884-10 (VDE V 0884-10): 2006-12 and DIN EN 61010-1
  - 2500 V<sub>RMS</sub> Isolation Rating per UL 1577
  - 4000 V<sub>PK</sub> Isolation Rating per CSA CA5A and IEC 60950-1

### 2 Applications

- Profibus
- Factory Automation
- Networked Sensors
- Motor and Motion Control
- HVA and Building Automation Networks
- Networked Security Stations

### 3 Description

The ISO1176 device is an isolated differential line transceiver designed for use in PROFIBUS applications. The device is ideal for long transmission lines because the ground loop is broken to provide for operation with a much larger common-mode voltage range. The symmetrical isolation barrier of each device is tested to provide 2500 V<sub>RMS</sub> of isolation per UL between the line transceiver and the logic level interface.

The galvanically isolated differential bus transceiver is an integrated circuit designed for bidirectional data communication on multipoint bus-transmission lines. The transceiver combines a galvanically isolated differential line driver and differential input line receiver. The driver has an active-high enable with isolated enable-state output on the ISODE pin (pin 10) to facilitate direction control. The driver differential outputs and the receiver differential inputs connect internally to form a differential input/output (I/O) bus port that is designed to offer minimum loading to the bus allowing up to 160 nodes.

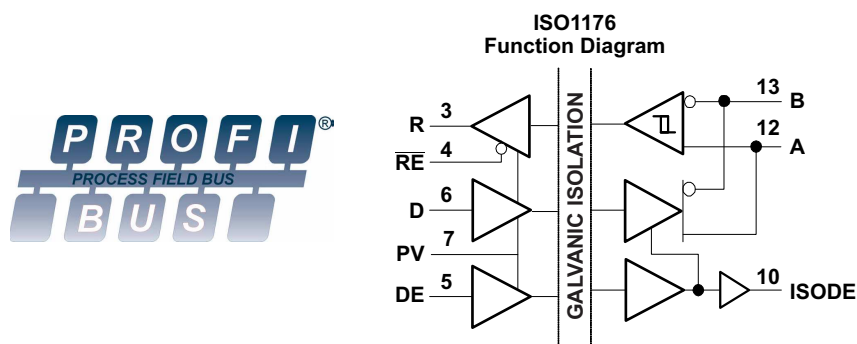
The PV pin (pin 7) is provided as a full-chip enable option. All device outputs become high impedance when a logic low is applied to the PV pin. For more information, see the function tables in [Device Functional Modes](#).

**Device Information<sup>(1)</sup>**

| PART NUMBER | PACKAGE   | BODY SIZE (NOM)    |
|-------------|-----------|--------------------|
| ISO1176     | SOIC (16) | 10.30 mm × 7.50 mm |

(1) For all available packages, see the orderable addendum at the end of the data sheet.

### Simplified Schematic



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## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

| Changes from Revision D (March 2010) to Revision E                                                                                                                                                                                                                                                                                                                                                   | Page |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|
| • Added <i>Pin Configuration and Functions</i> section, <i>ESD Ratings</i> table, <i>Feature Description</i> section, <i>Device Functional Modes</i> , <i>Application and Implementation</i> section, <i>Power Supply Recommendations</i> section, <i>Layout</i> section, <i>Device and Documentation Support</i> section, and <i>Mechanical, Packaging, and Orderable Information</i> section ..... | 1    |
| • VDE standard changed to DIN V VDE V 0884-10 (VDE V 0884-10): 2006-12 .....                                                                                                                                                                                                                                                                                                                         | 1    |
| • Changed the IEC 60664-1 Ratings Table. Basic isolation group SPECIFICATION entry From: IIIa To: II .....                                                                                                                                                                                                                                                                                           | 19   |

| Changes from Revision C (October 2008) to Revision D                                      | Page |
|-------------------------------------------------------------------------------------------|------|
| • Added 560-Vpeak $V_{IORM}$ to the first Features List .....                             | 1    |
| • Added UL 1577, IEC 60747-5-2 (VDE 0884, Rev. 2), to the Features List .....             | 1    |
| • Added Input pulse width MIN = 10 ns to the RECOMMENDED OPERATING CONDITIONS table ..... | 5    |
| • Added the CSA column to the Regulatory Information table .....                          | 20   |
| • Changed the ISO1176 "Sticky Bit" Issue section .....                                    | 26   |

| Changes from Revision B (June 2008) to Revision C                                                                                                            | Page |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------|------|
| • Changed the text in the second paragraph of the DESCRIPTION From: "whenever the driver is disabled or $V_{CC2}$ = 0" To: "allowing up to 160 nodes." ..... | 1    |

| Changes from Revision A (May 2008) to Revision B                                                                      | Page |
|-----------------------------------------------------------------------------------------------------------------------|------|
| • Changed L(IO1), Minimum air gap (Clearance) in the PACKAGE CHARACTERISTICS table From: MIN = 7.7mm To: 8.34mm ..... | 19   |

**Changes from Original (March 2008) to Revision A**
**Page**

|                                                                                                         |                    |
|---------------------------------------------------------------------------------------------------------|--------------------|
| • Added 3.3-V Inputs are 5-V Tolerant to the Features List.....                                         | <a href="#">1</a>  |
| • Added the Bus-Pin ESD Protection bullet and sub bullets to the Features List.....                     | <a href="#">1</a>  |
| • Added Bus pins to GND1 and Bus pins to GND2 to the ESD information in the Handling Rating table ..... | <a href="#">5</a>  |
| • Added the APPLICATION INFORMATION section.....                                                        | <a href="#">24</a> |

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## ISO1176

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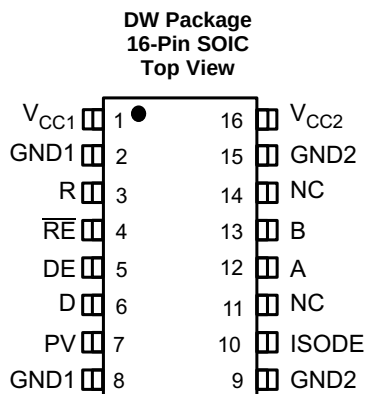
[www.ti.com](http://www.ti.com)

## 5 Description (continued)

Any cabled I/O can be subjected to electrical noise transients from various sources. These noise transients can cause damage to the transceiver and/or nearby sensitive circuitry if they are of sufficient magnitude and duration. The ISO1176 can significantly reduce the risk of data corruption and damage to expensive control circuits.

The device is characterized for operation over the ambient temperature range of  $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$ .

## 6 Pin Configuration and Functions



**Pin Functions**

| PIN                    |        | I/O | DESCRIPTION                                                                                                                |
|------------------------|--------|-----|----------------------------------------------------------------------------------------------------------------------------|
| NAME                   | NO.    |     |                                                                                                                            |
| A                      | 12     | I/O | Noninverting bus output                                                                                                    |
| B                      | 13     | I/O | Inverting bus output                                                                                                       |
| D                      | 6      | I   | Driver input                                                                                                               |
| DE                     | 5      | I   | Driver logic-high enable                                                                                                   |
| GND1                   | 2, 8   | —   | Logic-side ground; internally connected                                                                                    |
| GND2                   | 9, 15  | —   | Bus-side ground; internally connected                                                                                      |
| ISODE                  | 10     | —   | Bus-side driver enable output                                                                                              |
| NC                     | 11, 14 | —   | Not connected internally; may be left floating                                                                             |
| PV                     | 7      | I   | ISO1176 chip enable, logic high applied immediately after power up for device operation. A logic low 3-states all outputs. |
| R                      | 3      | O   | Receiver output                                                                                                            |
| $\overline{\text{RE}}$ | 4      | I   | Receiver logic-low enable                                                                                                  |
| V <sub>CC1</sub>       | 1      | —   | Logic side power supply                                                                                                    |
| V <sub>CC2</sub>       | 16     | —   | Bus side power supply                                                                                                      |

## 7 Specifications

### 7.1 Absolute Maximum Ratings

over operating junction temperature range unless otherwise noted<sup>(1)</sup>

|           |                               |                          | MIN  | MAX | UNIT |
|-----------|-------------------------------|--------------------------|------|-----|------|
| $V_{CC}$  | Supply voltage <sup>(2)</sup> | $V_{CC1}$ , $V_{CC2}$    | −0.5 | 7   | V    |
| $V_O$     | Voltage at any bus I/O pins   |                          | −9   | 14  | V    |
| $V_I$     | Voltage input                 | D, DE or $\overline{RE}$ | −0.5 | 7   | V    |
| $I_O$     | Receiver output current       |                          | −10  | 10  | mA   |
| $T_J$     | Maximum junction temperature  |                          |      | 170 | °C   |
| $T_{stg}$ | Storage temperature           |                          | −65  | 150 | °C   |

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. All voltage values are with respect to the network ground terminal unless otherwise noted.
- (2) All voltage values except differential I/O bus voltages are with respect to the referenced network ground terminal and are peak voltage values.

### 7.2 ESD Ratings

|             |                         |                                                                                          | VALUE             | UNIT   |
|-------------|-------------------------|------------------------------------------------------------------------------------------|-------------------|--------|
| $V_{(ESD)}$ | Electrostatic discharge | Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>                        | Bus pins to 2, 8  | ±6000  |
|             |                         |                                                                                          | Bus pins to 9, 15 | ±16000 |
|             |                         |                                                                                          | All pins          | ±4000  |
|             |                         | Charged device model (CDM), per JEDEC specification JESD22-C101, all pins <sup>(2)</sup> |                   | ±1000  |
|             |                         | Machine model (MM), per ANSI/ESDS5.2-1996, all pins                                      |                   | ±200   |

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 7.3 Recommended Operating Conditions

|          |                                                             |                     | MIN           | NOM | MAX           | UNIT |
|----------|-------------------------------------------------------------|---------------------|---------------|-----|---------------|------|
| $V_{CC}$ | Logic-side supply voltage, $V_{CC1}$ (with respect to GND1) |                     | 3.15          |     | 5.5           | V    |
|          | Bus-side supply voltage, $V_{CC2}$ (with respect to GND2)   |                     | 4.75          |     | 5.25          |      |
| $V_{CM}$ | Voltage at either bus I/O terminal                          | A, B                | −7            |     | 12            | V    |
| $V_{IH}$ | High-level input voltage                                    | PV, $\overline{RE}$ | 2             |     | 5.5           | V    |
|          |                                                             | D, DE               | 0.7 $V_{CC1}$ |     |               |      |
| $V_{IL}$ | Low-level input voltage                                     | PV, $\overline{RE}$ | 0             |     | 0.8           | V    |
|          |                                                             | D, DE               |               |     | 0.3 $V_{CC1}$ |      |
| $V_{ID}$ | Differential input voltage                                  | A with respect to B | −12           |     | 12            | V    |
| $I_O$    | Output current                                              | Driver              | −70           |     | 70            | mA   |
|          |                                                             | Receiver            | −8            |     | 8             |      |
|          | Input pulse width                                           |                     | 10            |     |               | ns   |
| $T_A$    | Ambient temperature                                         |                     | −40           | 25  | 85            | °C   |
| $T_J$    | Junction temperature                                        |                     |               |     | 150           | °C   |

## 7.4 Thermal Information

| THERMAL METRIC <sup>(1)</sup> |                                              | ISO1176      | UNIT |
|-------------------------------|----------------------------------------------|--------------|------|
|                               |                                              | DW [SOIC]    |      |
|                               |                                              | 16 PINS      |      |
| R <sub>θJA</sub>              | Junction-to-ambient thermal resistance       | High-K board | °C/W |
|                               |                                              | Low-K board  |      |
| R <sub>θJC(top)</sub>         | Junction-to-case (top) thermal resistance    | 41.4         | °C/W |
| R <sub>θJB</sub>              | Junction-to-board thermal resistance         | 46.4         | °C/W |
| ψ <sub>JT</sub>               | Junction-to-top characterization parameter   | 13.1         | °C/W |
| ψ <sub>JB</sub>               | Junction-to-board characterization parameter | 45.8         | °C/W |
| R <sub>θJC(bot)</sub>         | Junction-to-case (bottom) thermal resistance | N/A          | °C/W |

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

## 7.5 Electrical Characteristics: ISODE-Pin

over recommended operating conditions (unless otherwise noted)

| PARAMETER       |                           | TEST CONDITIONS          | MIN                    | TYP | MAX | UNIT |
|-----------------|---------------------------|--------------------------|------------------------|-----|-----|------|
| V <sub>OH</sub> | High-level output voltage | I <sub>OH</sub> = –8 mA  | V <sub>CC2</sub> – 0.8 | 4.6 |     | V    |
|                 |                           | I <sub>OH</sub> = –20 μA | V <sub>CC2</sub> – 0.1 | 5   |     |      |
| V <sub>OL</sub> | Low-level output voltage  | I <sub>OL</sub> = 8 mA   |                        | 0.2 | 0.4 | V    |
|                 |                           | I <sub>OL</sub> = 20 μA  |                        | 0   | 0.1 |      |

## 7.6 Supply Current

over recommended operating conditions (unless otherwise noted)

| PARAMETER        |                               | TEST CONDITIONS                             | MIN | TYP | MAX | UNIT |
|------------------|-------------------------------|---------------------------------------------|-----|-----|-----|------|
| I <sub>CC1</sub> | Logic-side RMS supply current | DE at 0 V                                   |     | 4   | 6   | mA   |
|                  |                               | DE at V <sub>CC1</sub> , 2 Mbps             |     | 5   |     |      |
|                  |                               | DE at V <sub>CC1</sub> , 25 Mbps            |     | 6   |     |      |
|                  |                               | DE at 0 V                                   |     | 7   | 10  |      |
|                  |                               | DE at V <sub>CC1</sub> , 2 Mbps             |     | 8   |     |      |
|                  |                               | DE at V <sub>CC1</sub> , 25 Mbps            |     | 11  |     |      |
| I <sub>CC2</sub> | Bus-side RMS supply current   | DE at 0 V                                   |     | 15  | 18  | mA   |
|                  |                               | DE at V <sub>CC1</sub> , 2 Mbps, 54-Ω load  |     | 70  |     |      |
|                  |                               | DE at V <sub>CC1</sub> , 25 Mbps, 54-Ω load |     | 75  |     |      |

## 7.7 Electrical Characteristics: Driver

over recommended operating conditions (unless otherwise noted)

| PARAMETER             |                                                                         | TEST CONDITIONS                                                                          | MIN                                                                                | TYP | MAX       | UNIT         |
|-----------------------|-------------------------------------------------------------------------|------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------|-----|-----------|--------------|
| $V_{OD}$              | Open-circuit differential output voltage                                | $ V_A - V_B $ , <a href="#">Figure 8</a>                                                 | 1.5                                                                                |     | $V_{CC2}$ | V            |
| $ V_{OD(SS)} $        | Steady-state differential output voltage magnitude                      | See <a href="#">Figure 9</a> and <a href="#">Figure 13</a>                               | 2.1                                                                                |     |           | V            |
|                       |                                                                         | Common-mode loading with $V_{test}$ from $-7$ V to $12$ V, See <a href="#">Figure 10</a> | 2.1                                                                                |     |           |              |
| $ \Delta V_{OD(SS)} $ | Change in steady-state differential output voltage between logic states | $R_L = 54\ \Omega$ , See <a href="#">Figure 11</a> and <a href="#">Figure 12</a>         | $-0.2$                                                                             |     | $0.2$     | V            |
| $V_{OC(SS)}$          | Steady-state common-mode output voltage                                 | $R_L = 54\ \Omega$ , See <a href="#">Figure 11</a> and <a href="#">Figure 12</a>         | 2                                                                                  |     | 3         | V            |
| $\Delta V_{OC(SS)}$   | Change in steady-state common-mode output voltage                       |                                                                                          | $-0.2$                                                                             |     | $0.2$     |              |
| $V_{OC(PP)}$          | Peak-to-peak common-mode output voltage                                 |                                                                                          |                                                                                    | 0.5 |           |              |
| $V_{OD(RING)}$        | Differential output voltage over- and undershoot                        | See <a href="#">Figure 13</a> and <a href="#">Figure 17</a>                              |                                                                                    |     | 10%       | $V_{OD(pp)}$ |
| $V_{I(HYS)}$          | Input voltage hysteresis                                                | See <a href="#">Figure 14</a>                                                            |                                                                                    | 150 |           | mV           |
| $I_I$                 | Input current                                                           | D, DE at $0$ V or $V_{CC1}$                                                              | $-10$                                                                              |     | 10        | $\mu A$      |
|                       |                                                                         | PV <sup>(1)</sup> at $0$ V or $V_{CC1}$                                                  |                                                                                    |     | 120       |              |
| $I_{O(OFF)}$          | Output current with power off                                           | $V_{CC} \leq 2.5$ V                                                                      | See receiver input current in <a href="#">Electrical Characteristics: Receiver</a> |     |           |              |
| $I_{OZ}$              | High-impedance state output current                                     | DE at $0$ V                                                                              |                                                                                    |     |           |              |
| $I_{OS(P)}$           | Peak short-circuit output current                                       | $V_{OS} = -7$ V to $12$ V                                                                | $-250$                                                                             |     | 250       | mA           |
| $I_{OS(SS)}$          | Steady-state short-circuit output current                               | DE at $V_{CC}$ , See <a href="#">Figure 15</a> and <a href="#">Figure 16</a>             |                                                                                    |     | 135       |              |
|                       |                                                                         | $V_{OS} = -7$ V, D at $V_{CC1}$                                                          | $-135$                                                                             |     |           |              |
| $C_{OD}$              | Differential output capacitance                                         |                                                                                          | See receiver $C_{IN}$ in <a href="#">Electrical Characteristics: Receiver</a>      |     |           |              |
| CMTI                  | Common-mode transient immunity                                          | See <a href="#">Figure 27</a>                                                            | 25                                                                                 |     |           | kV/ $\mu s$  |

(1) The PV pin has a 50-k $\Omega$  pullup resistor and leakage current depends on supply voltage.

## 7.8 Electrical Characteristics: Receiver

over recommended operating conditions (unless otherwise noted)

| PARAMETER                    |                                                     | TEST CONDITIONS                                                                                            |                                               | MIN                      | TYP             | MAX | UNIT          |
|------------------------------|-----------------------------------------------------|------------------------------------------------------------------------------------------------------------|-----------------------------------------------|--------------------------|-----------------|-----|---------------|
| $V_{IT(+)}$                  | Positive-going differential input voltage threshold | See Figure 22                                                                                              | $I_O = -8 \text{ mA}$                         |                          | -80             | -10 | mV            |
| $V_{IT(-)}$                  | Negative-going differential input voltage threshold |                                                                                                            | $I_O = 8 \text{ mA}$                          | -200                     | -120            |     | mV            |
| $V_{hys}$                    | Hysteresis voltage ( $V_{IT+} - V_{IT-}$ )          |                                                                                                            |                                               |                          | 40              |     | mV            |
| $V_{OH}$                     | High-level output voltage                           | $V_{CC1}$ at 3.3 V and $V_{CC2}$ at 5 V                                                                    | $V_{ID} = 200 \text{ mV}$ ,<br>See Figure 22  | $I_{OH} = -8 \text{ mA}$ | $V_{CC1} - 0.4$ | 3   | V             |
| $V_{OL}$                     | Low-level output voltage                            |                                                                                                            | $V_{ID} = -200 \text{ mV}$ ,<br>See Figure 22 | $I_{OL} = 8 \text{ mA}$  | $V_{CC1} - 0.1$ | 3.3 |               |
| $V_{OH}$                     | High-level output voltage                           | $V_{CC1}$ at 5 V and $V_{CC2}$ at 5 V                                                                      | $V_{ID} = 200 \text{ mV}$ ,<br>See Figure 22  | $I_{OH} = -8 \text{ mA}$ | $V_{CC1} - 0.8$ | 4.6 | V             |
| $V_{OL}$                     | Low-level output voltage                            |                                                                                                            | $V_{ID} = -200 \text{ mV}$ ,<br>See Figure 22 | $I_{OL} = 8 \text{ mA}$  | $V_{CC1} - 0.1$ | 5   |               |
| $I_A, I_B$                   | Bus pin input current                               | $V_I = -7 \text{ V}$ or $12 \text{ V}$ ,<br>Other input = $0 \text{ V}$                                    | $V_{CC} = 4.75 \text{ V}$ or $5.25 \text{ V}$ | -160                     |                 | 200 | $\mu\text{A}$ |
| $I_{A(OFF)}$<br>$I_{B(OFF)}$ |                                                     |                                                                                                            | $V_{CC2} = 0 \text{ V}$                       |                          |                 |     |               |
| $I_I$                        | Receiver enable input current                       | $\overline{RE} = 0 \text{ V}$                                                                              |                                               | -50                      |                 | 50  | $\mu\text{A}$ |
| $I_{OZ}$                     | High-impedance state output current                 | $\overline{RE} = V_{CC1}$                                                                                  |                                               | -1                       |                 | 1   | $\mu\text{A}$ |
| $R_{ID}$                     | Differential input resistance                       | A, B                                                                                                       |                                               | 48                       |                 |     | k $\Omega$    |
| $C_{ID}$                     | Differential input capacitance                      | Test input signal is a 1.5-MHz sine wave with<br>1 $V_{pp}$ amplitude, $C_D$ is measured across<br>A and B |                                               |                          | 7               | 10  | pF            |
| CMR                          | Common-mode rejection                               | See Figure 26                                                                                              |                                               |                          | 4               |     | V             |

## 7.9 Power Dissipation Characteristics

| PARAMETER |                   | VALUE                                                                                                                                  | UNIT      |
|-----------|-------------------|----------------------------------------------------------------------------------------------------------------------------------------|-----------|
| $P_D$     | Power Dissipation | $V_{CC1} = V_{CC2} = 5.25 \text{ V}$ , $T_J = 150^\circ\text{C}$ , $CL = 15 \text{ pF}$ ,<br>Input a 20 MHz 50% duty-cycle square wave | 220<br>mW |

## 7.10 Switching Characteristics: Driver

over recommended operating conditions (unless otherwise noted)

| PARAMETER                                                  |                                                            | TEST CONDITIONS                                                                                 | MIN  | TYP | MAX | UNIT          |
|------------------------------------------------------------|------------------------------------------------------------|-------------------------------------------------------------------------------------------------|------|-----|-----|---------------|
| $t_{PLH}, t_{PHL}$                                         | Propagation delay time                                     | See Figure 17                                                                                   |      |     | 35  | ns            |
| $t_{sk(p)}$                                                | Pulse skew ( $ t_{pHL} - t_{pLH} $ )                       |                                                                                                 |      | 2   | 5   | ns            |
| $t_{PLH}, t_{PHL}$                                         | Propagation delay time                                     |                                                                                                 |      |     | 40  | ns            |
| $t_{sk(p)}$                                                | Pulse skew ( $ t_{pHL} - t_{pLH} $ )                       |                                                                                                 |      | 2   | 5   | ns            |
| $t_r$                                                      | Differential output signal rise time                       |                                                                                                 | 2    | 3   | 7.5 | ns            |
| $t_f$                                                      | Differential output signal fall time                       |                                                                                                 | 2    | 3   | 7.5 | ns            |
| $t_{pDE}$                                                  | DE to ISODE prop delay                                     | See Figure 21                                                                                   |      |     | 30  | ns            |
| $t_{t(MLH)}, t_{t(MHL)}$                                   | Output transition skew                                     | See Figure 18                                                                                   |      |     | 1   | ns            |
| $t_{p(AZH)}, t_{p(BZH)}$<br>$t_{p(AZL)}, t_{p(BZL)}$       | Propagation delay time, high-impedance-to-active output    | $C_L = 50 \text{ pF}$ ,<br>$\overline{RE}$ at $0 \text{ V}$ ,<br>See Figure 19 and<br>Figure 20 |      |     | 80  | ns            |
| $t_{p(AHZ)}, t_{p(BHZ)}$<br>$t_{p(ALZ)}, t_{p(BLZ)}$       | Propagation delay time, active-to-high-impedance output    |                                                                                                 |      |     | 80  | ns            |
| $ t_{p(AZL)} - t_{p(BZH)} $<br>$ t_{p(AZH)} - t_{p(BZL)} $ | Enable skew time                                           |                                                                                                 | 0.55 |     | 1.5 | ns            |
| $t_{CFB}$                                                  | Time from application of short-circuit to current foldback | See Figure 16                                                                                   |      | 0.5 |     | $\mu\text{s}$ |
| $t_{TSD}$                                                  | Time from application of short-circuit to thermal shutdown | $T_A = 25^\circ\text{C}$ , See Figure 16                                                        | 100  |     |     | $\mu\text{s}$ |

## 7.11 Switching Characteristics: Receiver

over recommended operating conditions (unless otherwise noted)

| PARAMETER             |                                                             | TEST CONDITIONS                                    | MIN | TYP | MAX | UNIT |
|-----------------------|-------------------------------------------------------------|----------------------------------------------------|-----|-----|-----|------|
| $t_{pLH}$ , $t_{pHL}$ | Propagation delay time                                      | See <a href="#">Figure 23</a>                      |     |     | 50  | ns   |
| $t_{sk(p)}$           | Pulse skew ( $ t_{pHL} - t_{pLH} $ )                        |                                                    | 2   | 5   |     | ns   |
| $t_{pLH}$ , $t_{pHL}$ | Propagation delay time                                      |                                                    |     |     | 55  | ns   |
| $t_{sk(p)}$           | Pulse skew ( $ t_{pHL} - t_{pLH} $ )                        |                                                    | 2   | 5   |     | ns   |
| $t_r$                 | Output signal rise time                                     |                                                    | 2   | 4   |     | ns   |
| $t_f$                 | Output signal fall time                                     |                                                    | 2   | 4   |     | ns   |
| $t_{pZH}$             | Propagation delay time, high-impedance-to-high-level output | DE at $V_{CC1}$ ,<br>See <a href="#">Figure 24</a> | 13  | 25  |     | ns   |
| $t_{pHZ}$             | Propagation delay time, high-level-to-high-impedance output |                                                    | 13  | 25  |     | ns   |
| $t_{pZL}$             | Propagation delay time, high-impedance-to-low-level output  | DE at $V_{CC}$ ,<br>See <a href="#">Figure 25</a>  | 13  | 25  |     | ns   |
| $t_{pLZ}$             | Propagation delay time, low-level-to-high-impedance output  |                                                    | 13  | 25  |     | ns   |

## 7.12 Typical Characteristics

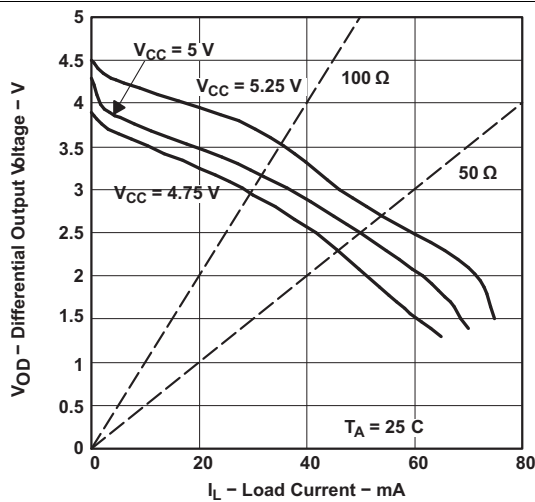


Figure 1. Differential Output Voltage vs Load Current

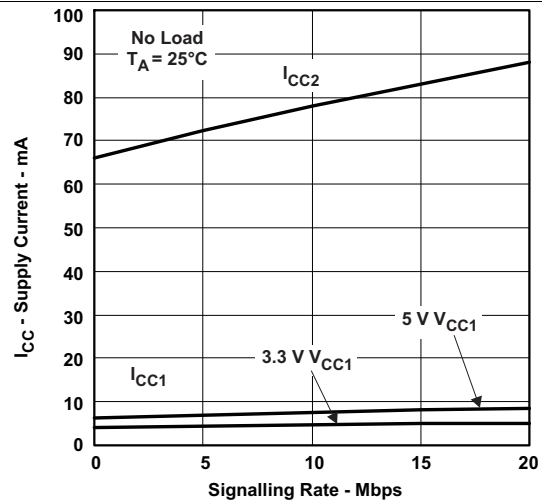


Figure 2. RMS Supply Current vs Signaling Rate

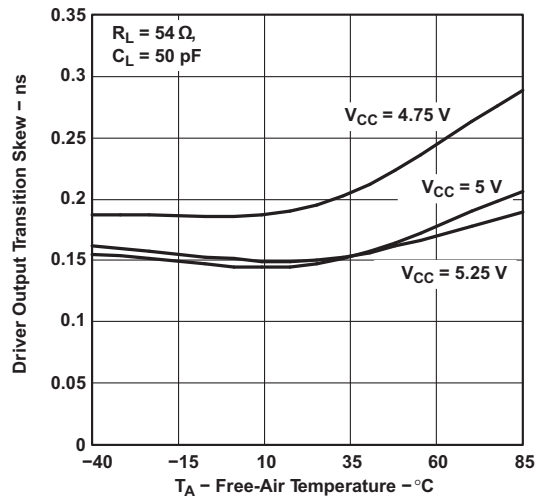


Figure 3. Driver Output Transition Skew vs Free-Air Temperature

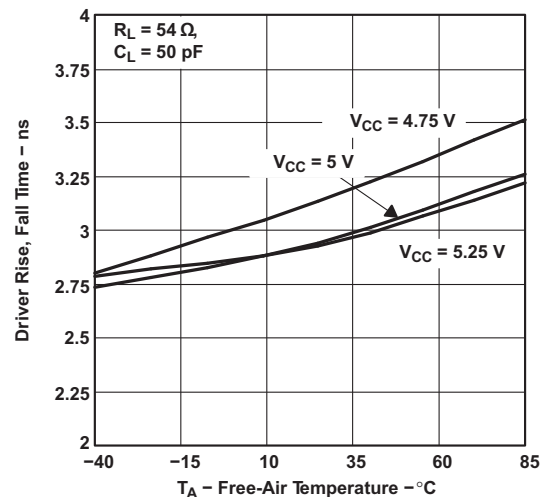


Figure 4. Driver Rise and Fall Time vs Free-Air Temperature

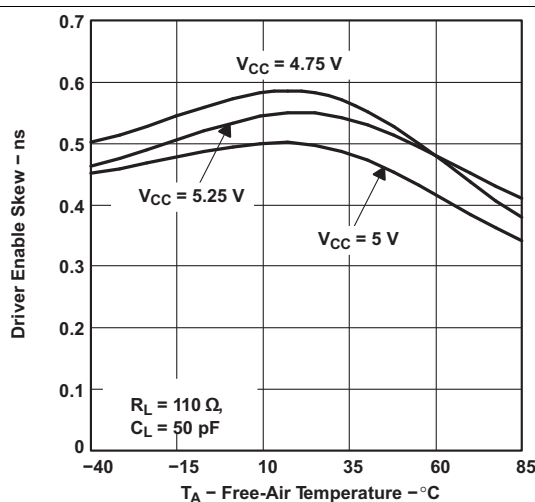


Figure 5. Driver Enable Skew vs Free-Air Temperature

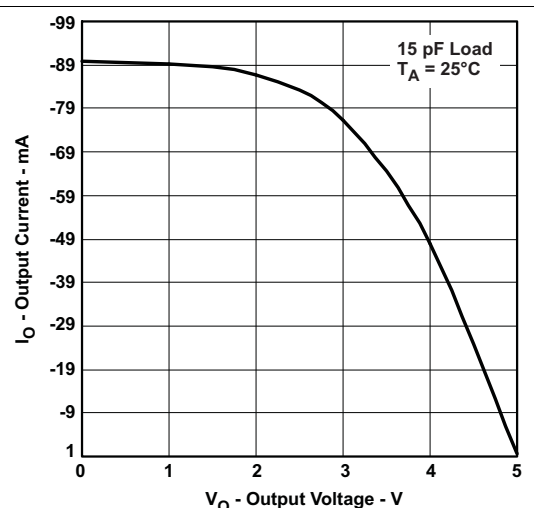


Figure 6. High-Level Output Voltage vs High-Level Output Current

## Typical Characteristics (continued)

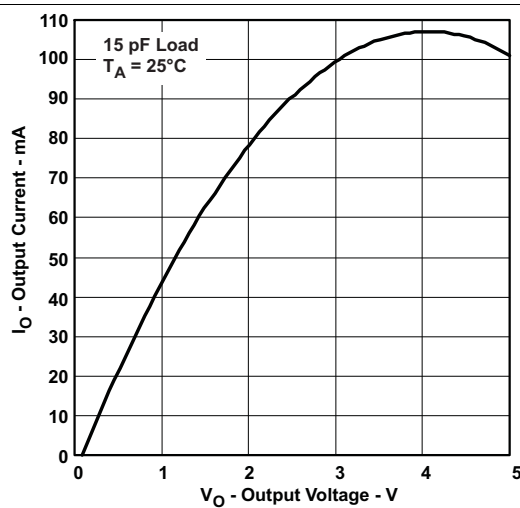


Figure 7. Low-Level Output Voltage vs Low-Level Output Current

## 8 Parameter Measurement Information

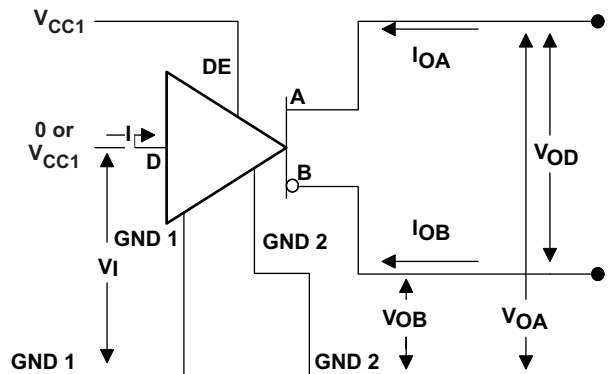


**Figure 8. Open Circuit Voltage Test Circuit**

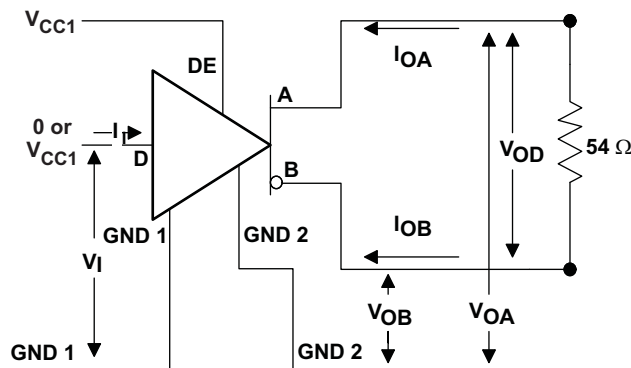


**Figure 9.  $V_{OD}$  Test Circuit**

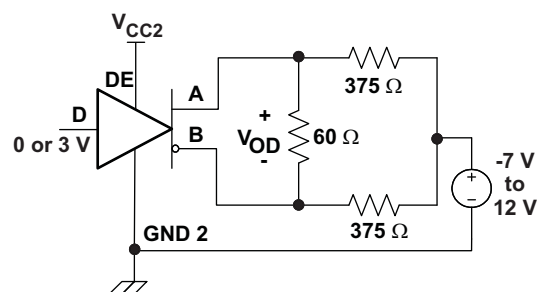


**Figure 10. Driver  $V_{OD}$  With Common-Mode Loading Test Circuit**

## Parameter Measurement Information (continued)

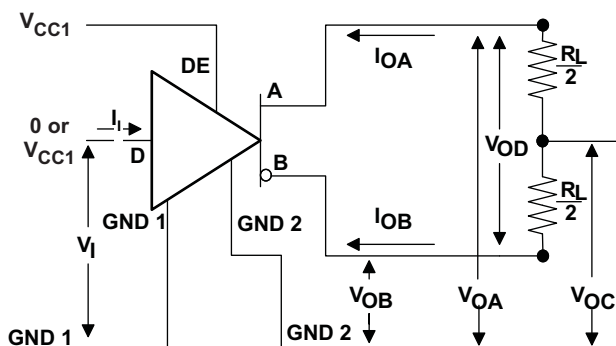


Figure 11. Driver  $V_{OD}$  and  $V_{OC}$  Without Common-Mode Loading Test Circuit

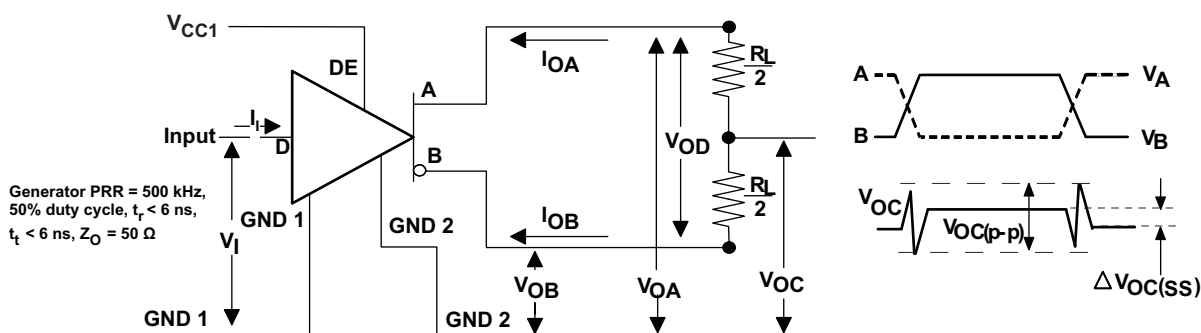


Figure 12. Steady-State Output Voltage Test Circuit and Voltage Waveforms

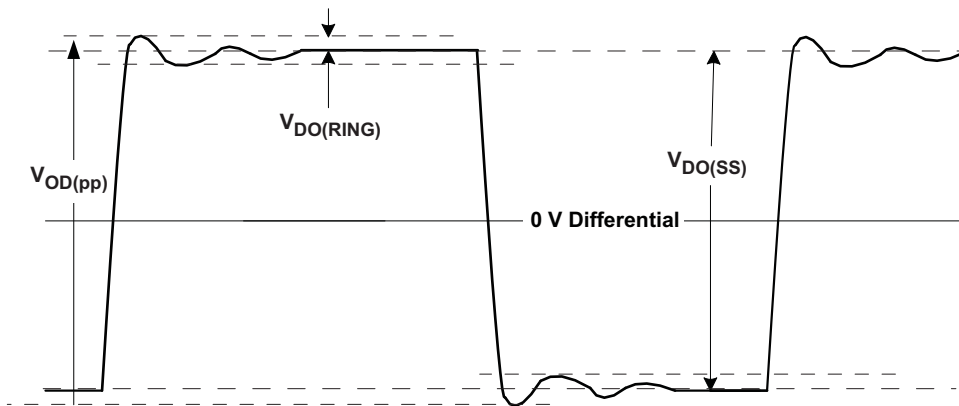
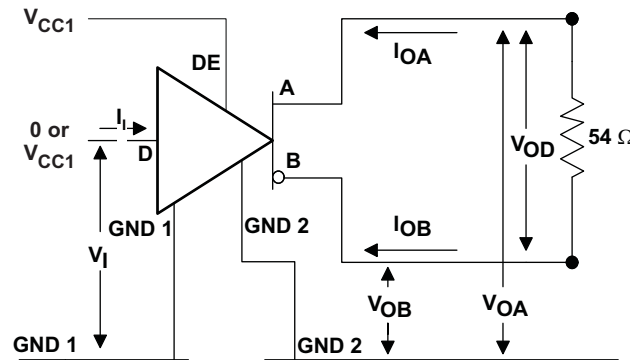
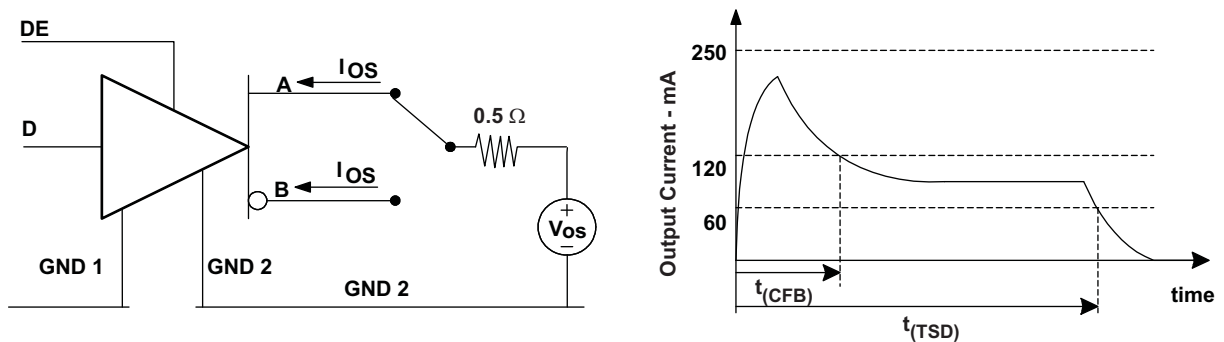
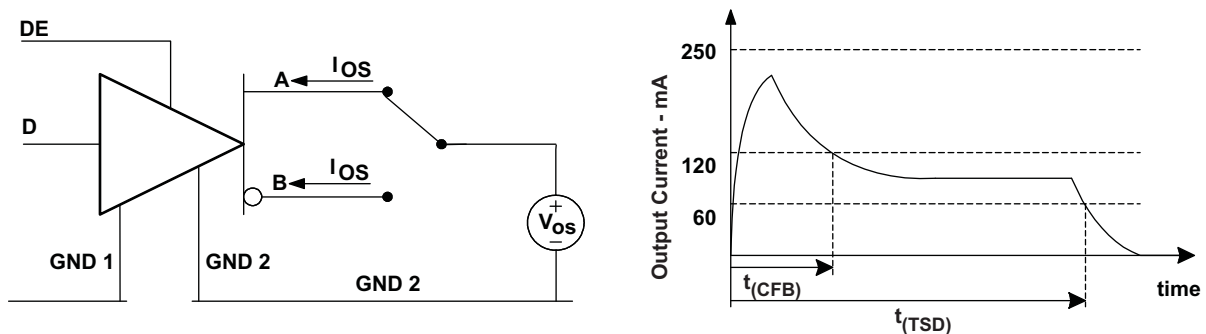
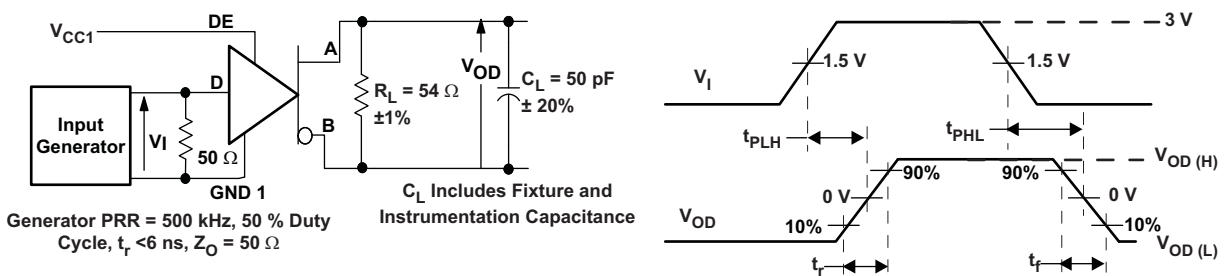


Figure 13.  $V_{OD(RING)}$  Waveform and Definitions

**Parameter Measurement Information (continued)**

**Figure 14. Input Voltage Hysteresis Test Circuit**

**Figure 15. Driver Short-Circuit Test Circuit and Waveforms (Short-Circuit Applied at Time t=0)**

**Figure 16.  $I_{OS(SS)}$  Steady State Short-Circuit Output Current Test Circuit**

**Figure 17. Driver Switching Test Circuit and Waveforms**

## Parameter Measurement Information (continued)

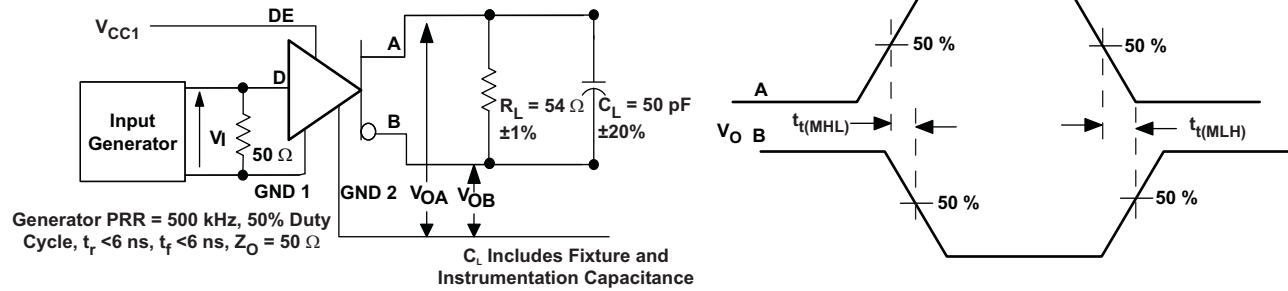


Figure 18. Driver Output Transition Skew Test Circuit and Waveforms

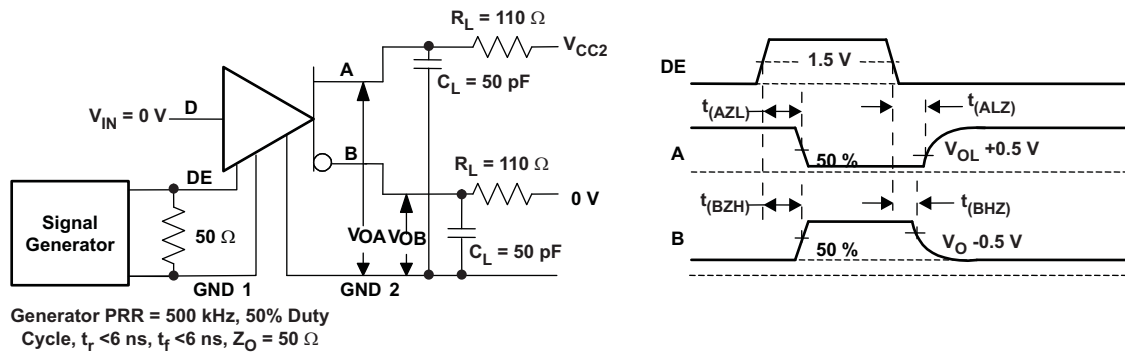


Figure 19. Driver Enable and Disable Test, D at Logic Low Test Circuit and Waveforms

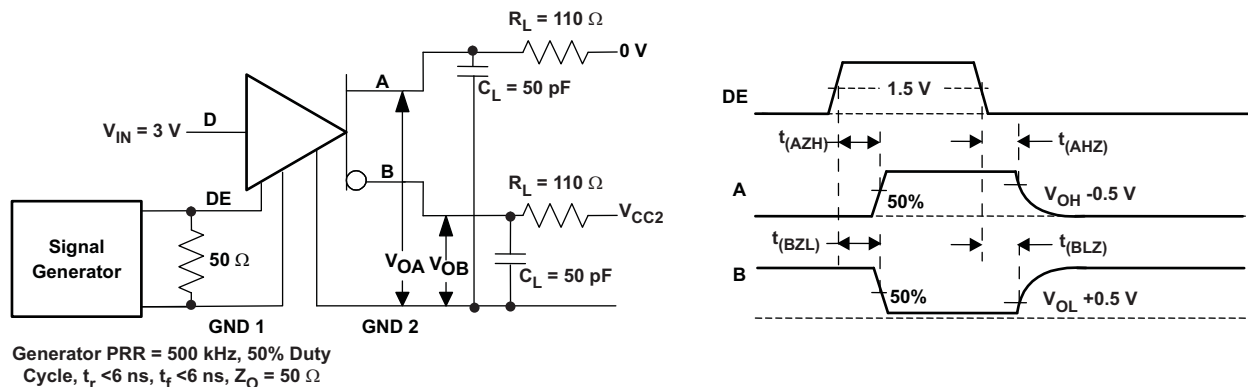
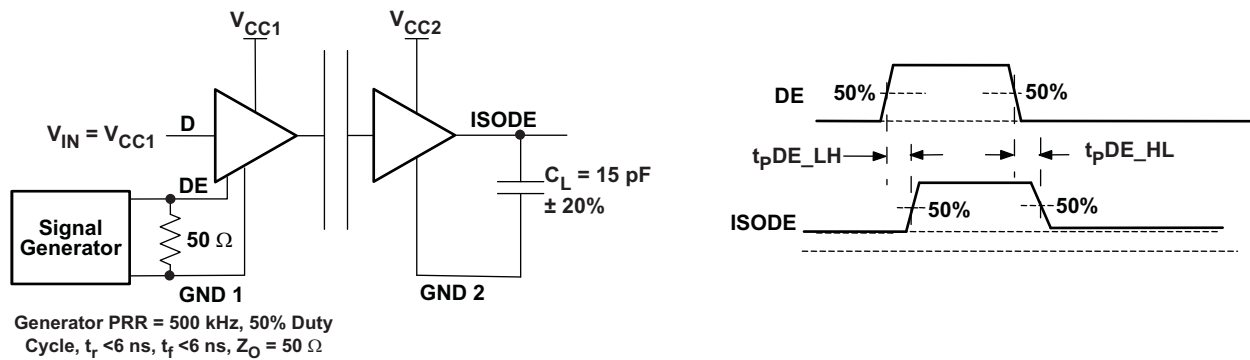
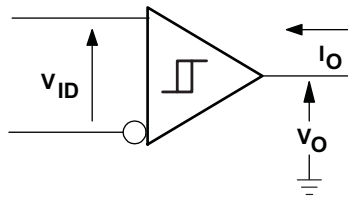
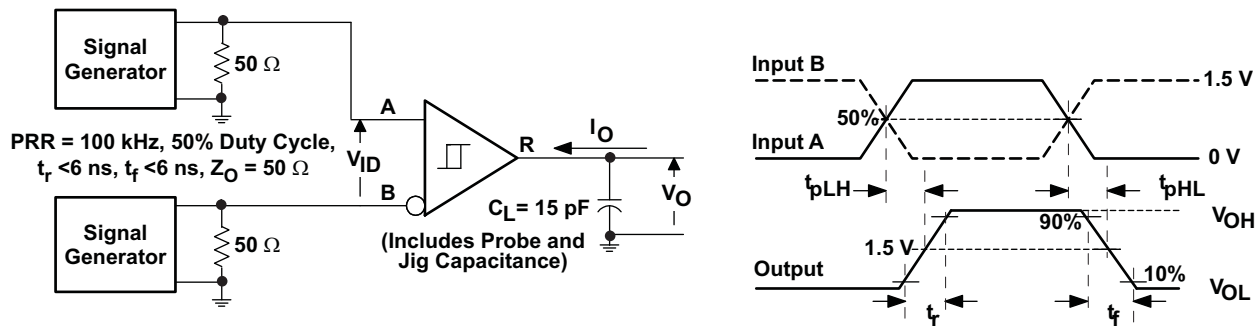
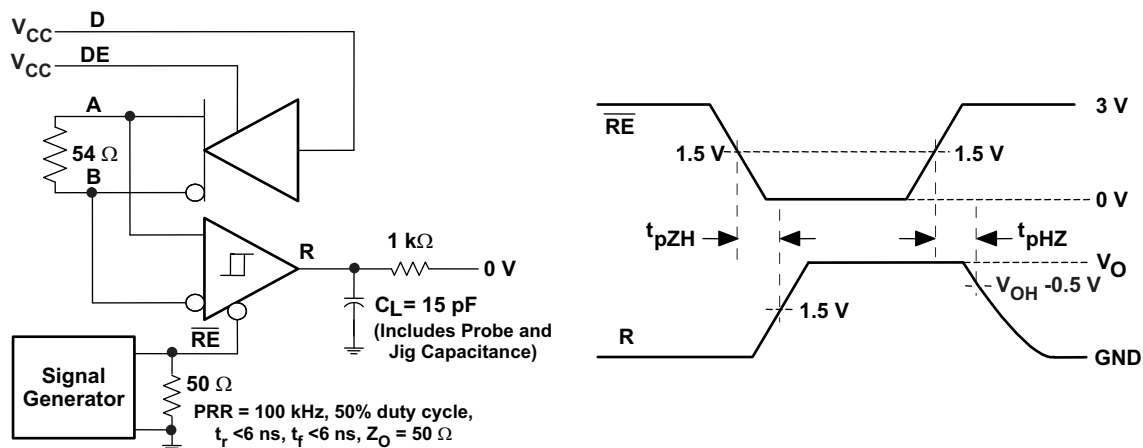


Figure 20. Driver Enable and Disable Test, D at Logic High Test Circuit and Waveforms

**Parameter Measurement Information (continued)**

**Figure 21. DE to ISODE Prop Delay Test Circuit and Waveforms**

**Figure 22. Receiver DC Parameter Definitions**

**Figure 23. Receiver Switching Test Circuit and Waveforms**

**Figure 24. Receiver Enable Test Circuit and Waveforms, Data Output High**

## Parameter Measurement Information (continued)

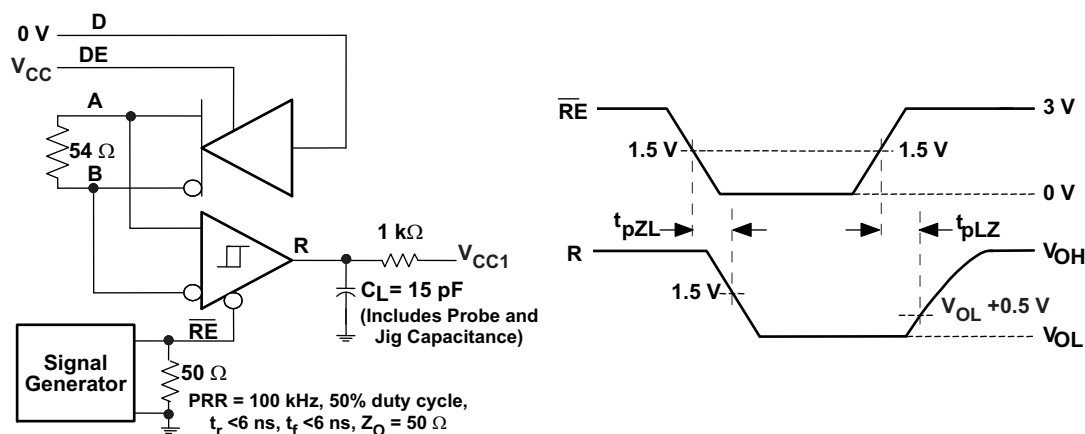


Figure 25. Receiver Enable Test Circuit and Waveforms, Data Output Low

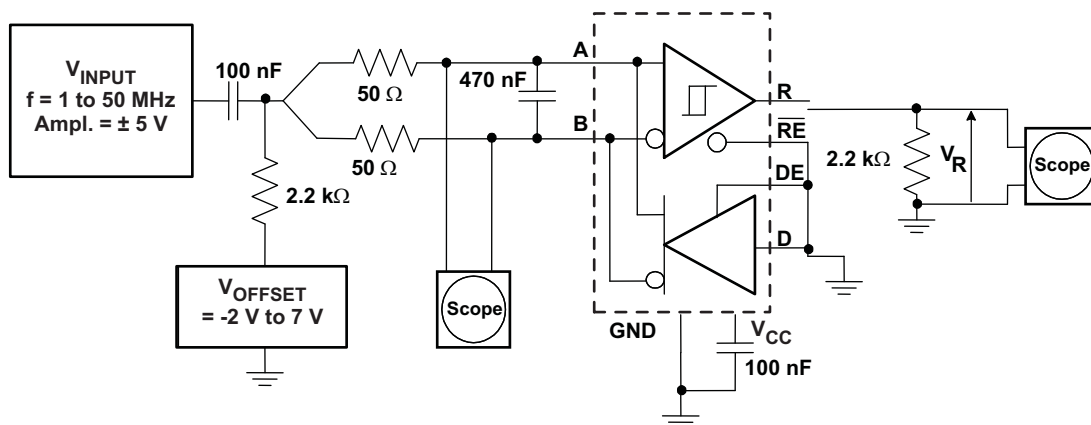


Figure 26. Common-Mode Rejection Test Circuit

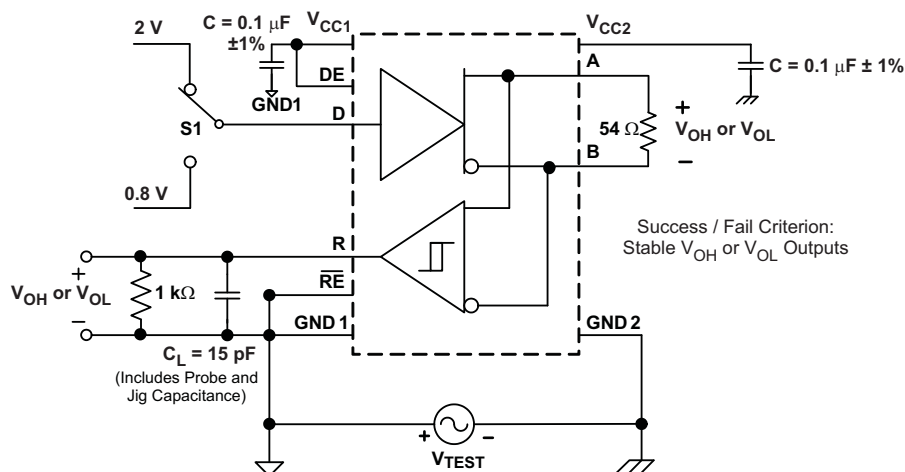


Figure 27. Common-Mode Transient Immunity Test Circuit



## 9.3 Feature Description

### 9.3.1 Insulation and Safety-Related Package Characteristics

over operating free-air temperature range (unless otherwise noted)

| PARAMETER       |                                                     | TEST CONDITIONS                                                                                                                                  | MIN   | TYP               | MAX | UNIT |
|-----------------|-----------------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------|-------|-------------------|-----|------|
| L(I01)          | Minimum air gap (Clearance)                         | Shortest terminal-to-terminal distance through air                                                                                               | 8.34  |                   |     | mm   |
| L(I02)          | Minimum external tracking (Creepage) <sup>(1)</sup> | Shortest terminal-to-terminal distance across the package surface                                                                                | 8.1   |                   |     | mm   |
| CTI             | Tracking resistance (Comparative Tracking Index)    | DIN IEC 60112 / VDE 0303 Part 1                                                                                                                  | ≥400  |                   |     | V    |
|                 | Minimum internal gap (Internal Clearance)           | Distance through the insulation                                                                                                                  | 0.008 |                   |     | mm   |
| R <sub>IO</sub> | Isolation resistance                                | Input to output, V <sub>IO</sub> = 500 V, T <sub>A</sub> = 25°C, all pins on each side of the barrier tied together creating a 2-terminal device |       | >10 <sup>12</sup> |     | Ω    |
| C <sub>IO</sub> | Barrier capacitance Input to output                 | V <sub>I</sub> = 0.4 sin (4E6πt)                                                                                                                 |       | 2                 |     | pF   |
| C <sub>I</sub>  | Input capacitance to ground                         | V <sub>I</sub> = 0.4 sin (4E6πt)                                                                                                                 |       | 2                 |     | pF   |

- (1) Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care must be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit-board (PCB) do not reduce this distance.  
Creepage and clearance on a PCB become equal according to the measurement techniques shown in the Isolation Glossary. Techniques such as inserting grooves and/or ribs on a PCB are used to help increase these specifications.

### 9.3.2 DIN V VDE V 0884-10 Insulation Characteristics

over recommended operating conditions (unless otherwise noted)

| PARAMETER         |                                    | TEST CONDITIONS                                                                                                    | SPECIFICATION    | UNIT            |
|-------------------|------------------------------------|--------------------------------------------------------------------------------------------------------------------|------------------|-----------------|
| V <sub>IOTM</sub> | Transient overvoltage              | t = 60 s                                                                                                           | 4000             | V <sub>PK</sub> |
| V <sub>IORM</sub> | Maximum working insulation voltage |                                                                                                                    | 560              | V <sub>PK</sub> |
| V <sub>PR</sub>   | Input to output test voltage       | Method b1, V <sub>PR</sub> = V <sub>IORM</sub> × 1.875, 100% Production test with t = 1 s, Partial discharge <5 pC | 1050             | V <sub>PK</sub> |
| R <sub>S</sub>    | Insulation resistance              | V <sub>IO</sub> = 500 V at T <sub>S</sub>                                                                          | >10 <sup>9</sup> | Ω               |
|                   | Pollution degree                   |                                                                                                                    | 2                |                 |

### 9.3.3 IEC 60664-1 Ratings Table

| PARAMETER                   | TEST CONDITIONS                            | SPECIFICATION |
|-----------------------------|--------------------------------------------|---------------|
| Basic isolation group       | Material group                             | II            |
| Installation classification | Rated mains voltage < 150 V <sub>RMS</sub> | I-IV          |
|                             | Rated mains voltage < 300 V <sub>RMS</sub> | I-III         |

### 9.3.4 Safety Limiting Values

Safety limiting intends to prevent potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the I/O can allow low resistance to ground or the supply and, without current-limiting, dissipate sufficient power to overheat the die and damage the isolation barrier potentially leading to secondary system failures.

| PARAMETER      |                                         | TEST CONDITIONS                                                                                            | MIN | TYP | MAX | UNIT |
|----------------|-----------------------------------------|------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| I <sub>S</sub> | Safety input, output, or supply current | DW-16<br>R <sub>θJA</sub> = 168°C/W, V <sub>I</sub> = 5.5 V, T <sub>J</sub> = 170°C, T <sub>A</sub> = 25°C |     |     | 157 | mA   |
| T <sub>S</sub> | Maximum case temperature                | DW-16                                                                                                      |     |     | 150 | °C   |

The safety-limiting constraint is the absolute maximum junction temperature specified in [Absolute Maximum Ratings](#). The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The assumed junction-to-air thermal resistance in [Thermal Information](#) is that of a device installed in the JESD51-3, Low Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages and is conservative.

The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance..

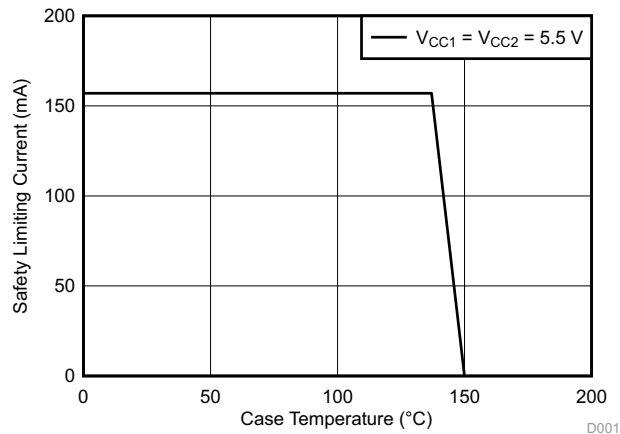


**Figure 28. DW-16  $R_{\theta JC}$  Thermal Derating Curve per VDE**

### 9.3.5 Regulatory Information

| VDE                                                                                                                     | CSA                                                                                                                             | UL                                                                    |
|-------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------|
| Certified according to DIN V VDE V 0884-10 (VDE V 0884-10):2006-12                                                      | Approved under CSA Component Acceptance Notice 5A and IEC 60950-1                                                               | Recognized under UL 1577 Component Recognition Program <sup>(1)</sup> |
| Basic insulation,<br>4000 V <sub>PK</sub> Maximum transient overvoltage,<br>560 V <sub>PK</sub> Maximum working voltage | 4000 V <sub>PK</sub> Isolation rating,<br>560 V <sub>PK</sub> Basic working voltage per CSA 60950-1-07 and IEC 60950-1 (2nd Ed) | Single Protection, 2500 V <sub>RMS</sub>                              |
| Certificate number: 40016131                                                                                            | Master contract number: 220991                                                                                                  | File number: E181974                                                  |

(1) Production tested  $\geq 3000$  Vrms for 1 second in accordance with UL 1577.

## 9.4 Device Functional Modes

**Table 1. Driver Function Table<sup>(1)</sup>**

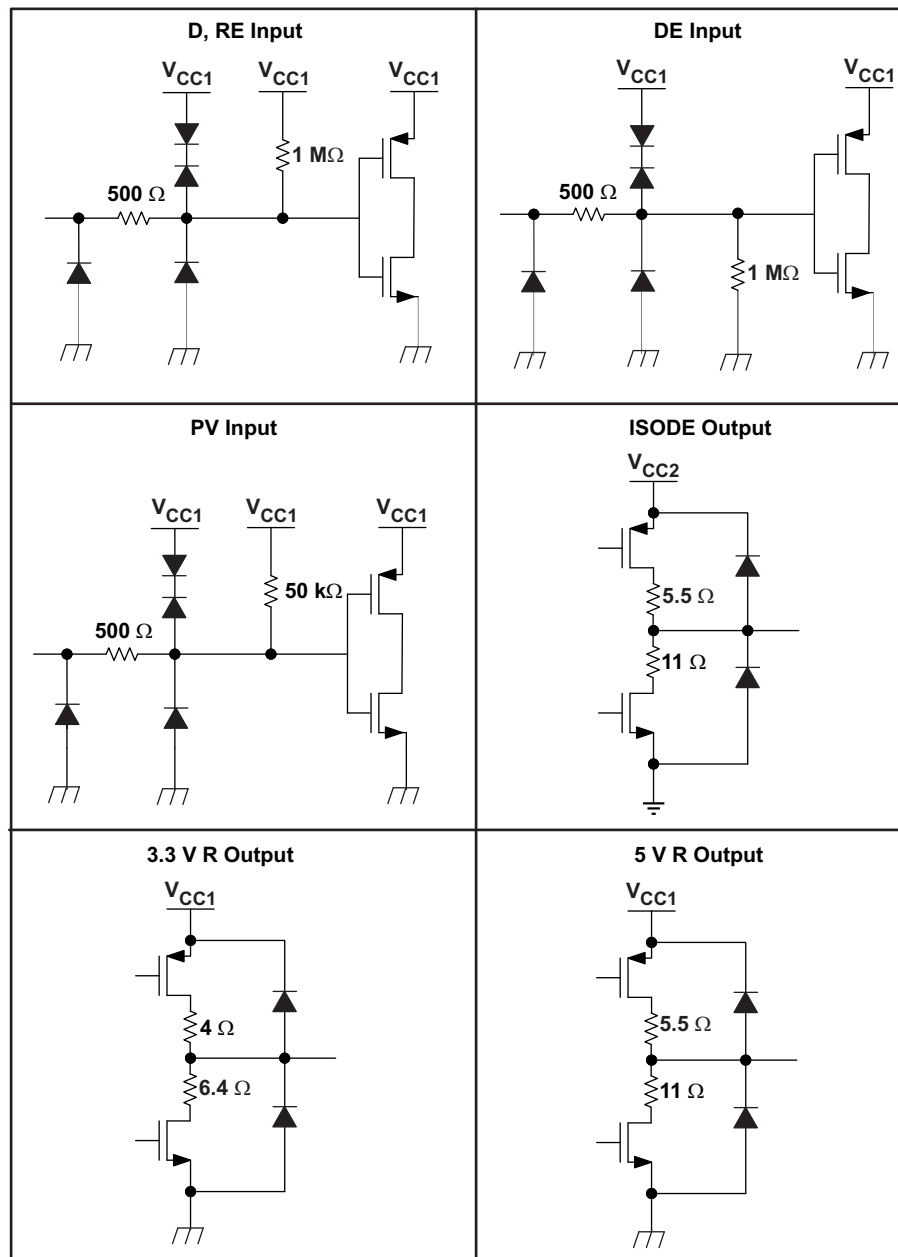
| V <sub>CC1</sub> | V <sub>CC2</sub> | POWER<br>VALID<br>(PV)<br>(ISO1176) | INPUT<br>(D) | ENABLE<br>INPUT<br>(DE) | ENABLE OUTPUT<br>(ISODE) | OUTPUTS |   |
|------------------|------------------|-------------------------------------|--------------|-------------------------|--------------------------|---------|---|
|                  |                  |                                     |              |                         |                          | A       | B |
| PU               | PU               | H or open                           | H            | H                       | H                        | H       | L |
| PU               | PU               | H or open                           | L            | H                       | H                        | L       | H |
| PU               | PU               | H or open                           | X            | L                       | L                        | Z       | Z |
| PU               | PU               | H or open                           | X            | open                    | L                        | Z       | Z |
| PU               | PU               | H or open                           | open         | H                       | H                        | H       | L |
| PD               | PU               | X                                   | X            | X                       | L                        | Z       | Z |
| PU               | PD               | X                                   | X            | X                       | L                        | Z       | Z |
| PD               | PD               | X                                   | X            | X                       | L                        | Z       | Z |
| X                | X                | L                                   | X            | X                       | L                        | Z       | Z |

(1) PU = powered up, PD = powered down, H = high level, L = low level, X = don't care, Z = high impedance (off)

**Table 2. Receiver Function Table<sup>(1)</sup>**

| V <sub>CC1</sub> | V <sub>CC2</sub> | POWER VALID<br>(PV) (ISO1176) | DIFFERENTIAL INPUT<br>V <sub>ID</sub> = (V <sub>A</sub> – V <sub>B</sub> ) | ENABLE<br>(RE) | OUTPUT<br>(R) |
|------------------|------------------|-------------------------------|----------------------------------------------------------------------------|----------------|---------------|
| PU               | PU               | H or open                     | –0.01 V ≤ V <sub>ID</sub>                                                  | L              | H             |
| PU               | PU               | H or open                     | –0.2 V < V <sub>ID</sub> < –0.01 V                                         | L              | ?             |
| PU               | PU               | H or open                     | V <sub>ID</sub> ≤ –0.2 V                                                   | L              | L             |
| PU               | PU               | H or open                     | X                                                                          | H              | Z             |
| PU               | PU               | H or open                     | X                                                                          | open           | Z             |
| PU               | PU               | H or open                     | Open-circuit                                                               | L              | H             |
| PU               | PU               | H or open                     | Short-circuit                                                              | L              | H             |
| PU               | PU               | H or open                     | Idle (terminated) bus                                                      | L              | H             |
| PD               | PU               | X                             | X                                                                          | X              | Z             |
| PU               | PD               | H or open                     | X                                                                          | L              | H             |
| PD               | PD               | X                             | X                                                                          | X              | Z             |
| X                | X                | L                             | X                                                                          | X              | Z             |

(1) PU = powered up, PD = powered down, H = high level, L = low level, X = don't care, Z = high impedance (off), ? = indeterminate


**Figure 29. Equivalent I/O Schematics**

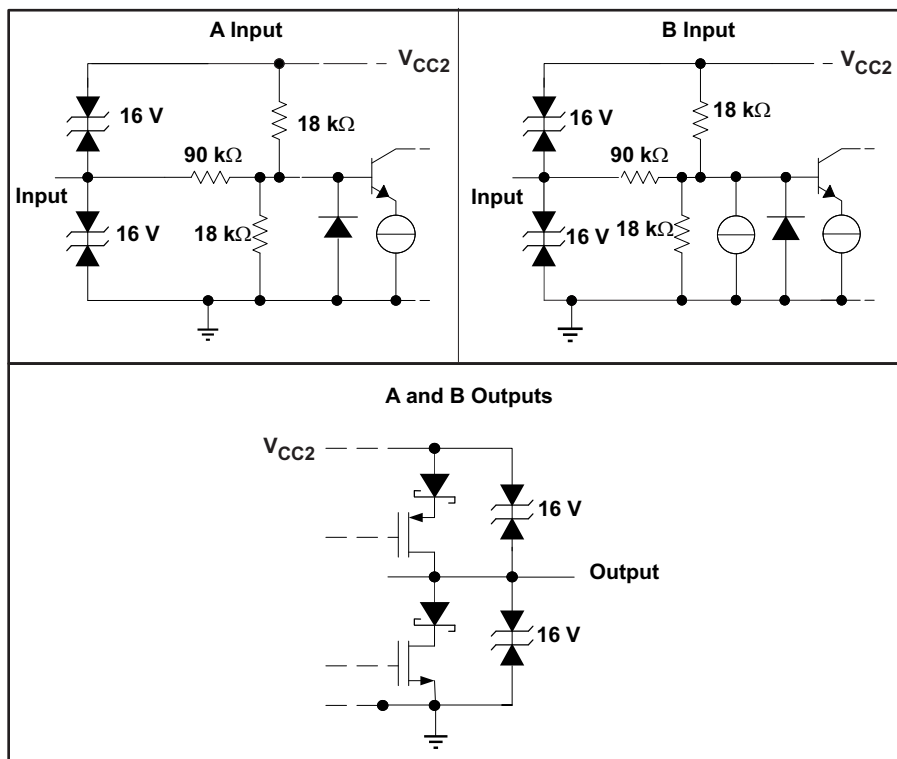


**Figure 30. Equivalent I/O Schematics for A and B Inputs and Outputs**

## 10 Application and Implementation

### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 10.1 Application Information

The ISO1176 device consists of a RS-485 transceiver, commonly used for asynchronous data transmissions. For half-duplex transmission, only one pair is shared for both transmission and reception of data. To eliminate line reflections, each cable end is terminated with a termination resistor,  $R(T)$ , whose value matches the characteristic impedance,  $Z_0$ , of the cable. This method, known as parallel termination, allows for higher data rates over longer cable length.

### 10.2 Typical Application

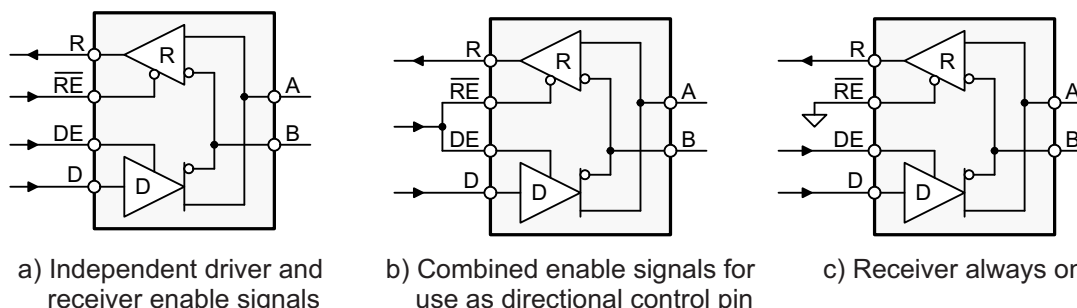


Figure 31. Half-Duplex Transceiver Configurations

#### 10.2.1 Design Requirements

RS-485 is a robust electrical standard suitable for long-distance networking that may be used in a wide range of applications with varying requirements, such as distance, data rate, and number of nodes.

Table 3. Design Parameters

| PARAMETER                     | VALUE         |
|-------------------------------|---------------|
| Pullup and Pulldown Resistors | 1 kΩ to 10 kΩ |
| Decoupling Capacitors         | 100 nF        |

#### 10.2.2 Detailed Design Procedure

Isolating of a circuit insulates it from other circuits and earth, so that noise voltage develops across the insulation rather than circuit components. The most common noise threat to data-line circuits is voltage surges or electrical fast transients that occur after installation. The transient ratings of the ISO1176 standard are sufficient for all but the most severe installations. However, some equipment manufacturers use ESD generators to test equipment transient susceptibility. This practice can exceed insulation ratings. ESD generators simulate static discharges that may occur during device or equipment handling with low-energy but high-voltage transients.

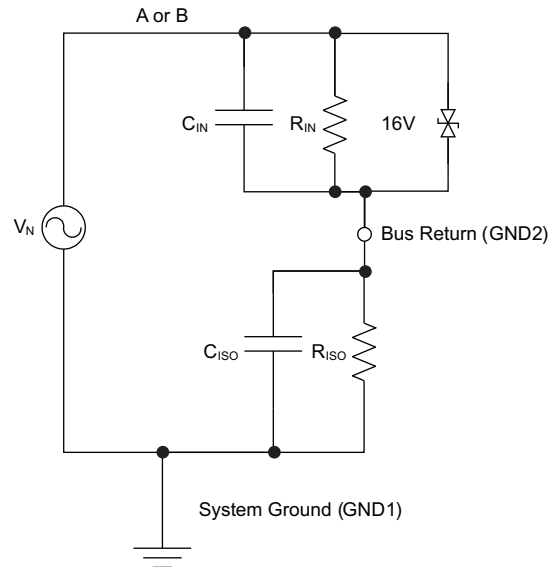


**Figure 32. Device Model for Static Discharge Testing**

Figure 32 models the ISO1176 bus IO connected to a noise generator.  $C_{IN}$  and  $R_{IN}$  is the device, and any other stray or added capacitance or resistance across the A or B pin to GND2.  $C_{ISO}$  and  $R_{ISO}$  is the capacitance and resistance between GND1 and GND2 of the ISO1176, plus those of any other insulation (transformer, and so forth). Stray inductance is assumed to be negligible.

#### 10.2.2.1 Transient Voltages

From this model, the voltage at the isolated bus return is

$$V_{GND2} = V_N \frac{Z_{ISO}}{Z_{ISO} + Z_{IN}} \quad (1)$$

and is always less than 16 V from  $V_N$ . If the ISO1176 is tested as a stand-alone device,

- $R_{IN} = 6 \times 10^4 \Omega$ ,
- $C_{IN} = 16 \times 10^{-12} \text{ F}$ ,
- $R_{ISO} = 10^9 \Omega$  and
- $C_{ISO} = 10^{-12} \text{ F}$ .

Notice from Figure 32 that the resistor ratio determines the voltage ratio at low frequencies, and that the inverse capacitance ratio determines the voltage ratio at high frequencies. In the stand-alone case and for low frequencies,

$$\frac{V_{GND2}}{V_N} = \frac{R_{ISO}}{R_{ISO} + R_{IN}} = \frac{10^9}{10^9 + 6 \times 10^4} \quad (2)$$

or essentially all of the noise appears across the barrier.

At high frequencies,

$$\frac{V_{GND2}}{V_N} = \frac{1/C_{ISO}}{1/C_{ISO} + 1/C_{IN}} = \frac{1}{1 + C_{ISO}/C_{IN}} = \frac{1}{1 + 1/16} = 0.94 \quad (3)$$

and 94% of  $V_N$  appears across the barrier. As long as  $R_{ISO}$  is greater than  $R_{IN}$  and  $C_{ISO}$  is less than  $C_{IN}$ , most of the transient noise appears across the isolation barrier, as it should.

Using ESD generators to test equipment transient susceptibility, or considering product claims of ESD ratings greater than the barrier transient ratings of an isolated interface is not recommended. ESD is best managed through recessing or covering connector pins in a conductive connector shell, and by proper installer training.

### 10.2.2.2 ISO1176 "Sticky Bit" Issue (Under Certain Conditions)

**Summary:** In applications with sufficient differential noise on the bus, the output of the ISO1176 receiver may "stick" at an incorrect state for up to 30  $\mu$ s.

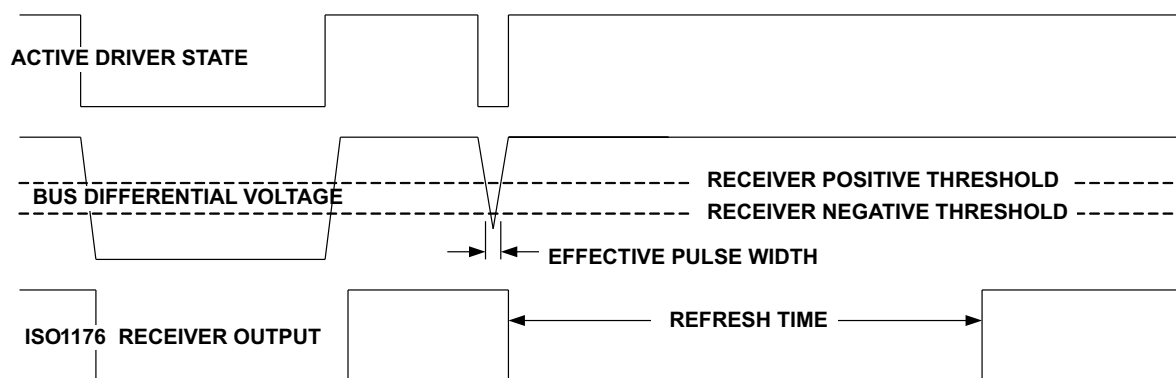
**Description:** The ISO1176 isolated Profibus (RS-485) transceiver is rated for signaling up to 40 Mbps on twisted-pair bus lines. The receiver thresholds comply with RS-485 and Profibus specifications; an input differential voltage  $V_{ID} = V_A - V_B > 200$  mV causes a logic High on the R output, and  $V_{ID} < -200$  mV causes a logic Low on the R output. To assure a known receiver output when the bus is shorted or idle, the upper threshold is set below zero, such that  $V_{ID} = 0$  mV causes a logic High on the R output. The data sheet specifies a typical upper threshold ( $V_{IT+}$ ) of  $-80$  mV and a typical lower threshold ( $V_{IT-}$ ) of  $-120$  mV.

At a signaling rate of 40 Mbps, each valid data bit has a duration of 25 ns. At typical Profibus signaling rates of 12 Mbps or lower, each valid data bit has a duration of 83 ns or more. The ISO1176 correctly sets the R output for each of these valid data bits.

In applications with a high degree of differential noise on the bus lines, it is possible to get short periods when an invalid bus voltage triggers a change in state of the internal receiver circuits. An issue with the digital isolation channel in the ISO1176 may cause the invalid receiver state to "stick" rather than immediately transition back to the correct state. The receiver output will always transition to the correct state, but may stick in the incorrect state for up to 30  $\mu$ s. This can cause a temporary loss of data.

Figure 33 shows two cases which could result in temporary loss of data.

#### Case 1



#### Case 2

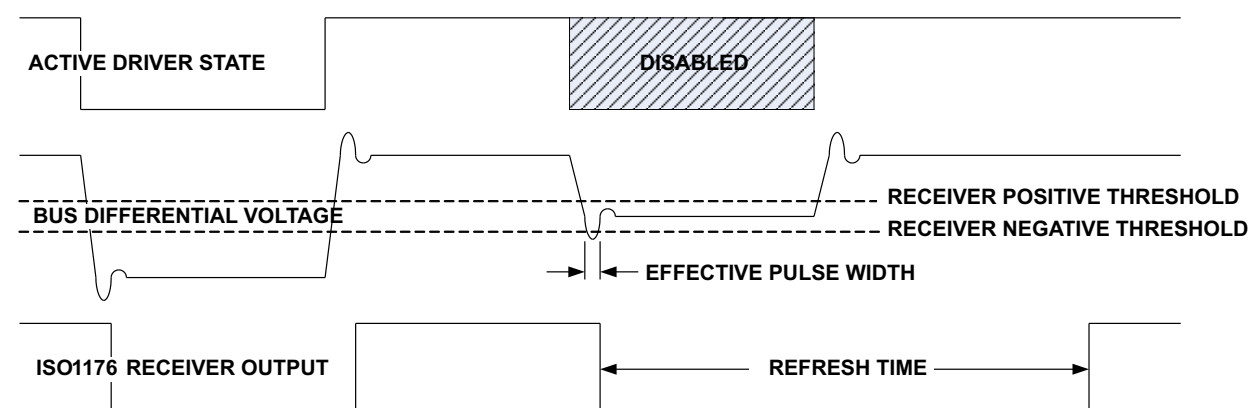


**Figure 33. "Sticky Bit" Issue Waveforms**

### 10.2.3 Application Curve

At maximum working voltage, ISO1176 isolation barrier has more than 28 years of life.

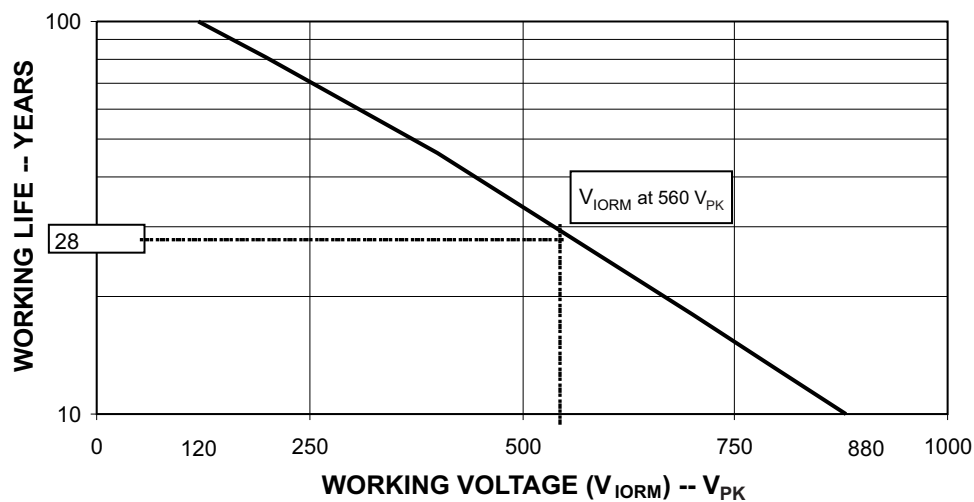


**Figure 34. Time-Dependent Dielectric Breakdown Test Results**

## 11 Power Supply Recommendations

To ensure reliable operation at all data rates and supply voltages, TI recommends a 0.1- $\mu$ F bypass capacitor at input and output supply pins ( $V_{CC1}$  and  $V_{CC2}$ ). The capacitors should be placed as close to the supply pins as possible. If only a single primary-side power supply is available in an application, isolated power can be generated for the secondary-side with the help of a transformer driver such as TI's [SN6501](#). For such applications, detailed power supply design and transformer selection recommendations are available in SN6501 data sheet ([SLLSEA0](#)).

## 12 Layout

### 12.1 Layout Guidelines

ON-chip IEC-ESD protection is good for laboratory and portable equipment but never sufficient for EFT and surge transients occurring in industrial environments. Therefore, robust and reliable bus node design requires the use of external transient protection devices. Because ESD and EFT transients have a wide frequency bandwidth from approximately 3-MHz to 3-GHz, high-frequency layout techniques must be applied during PCB design. A minimum of four layers is required to accomplish a low EMI PCB design (see [Figure 35](#)).

- Layer stacking should be in the following order (top-to-bottom): high-speed signal layer, ground plane, power plane, and low-frequency signal layer.
- Placing a solid ground plane next to the high-speed signal layer establishes controlled impedance for transmission line interconnects and provides an excellent low-inductance path for the return current flow.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance of approximately 100 pF/in<sup>2</sup>.
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links usually have margin to tolerate discontinuities such as vias.
- Place the protection circuitry close to the bus connector to prevent noise transients from penetrating your board.
- Use  $V_{CC}$  and ground planes to provide low-inductance. High-frequency currents might follow the path of least inductance and not necessarily the path of least resistance.
- Design the protection components into the direction of the signal path. Do not force the transient currents to divert from the signal path to reach the protection device.
- Apply 0.1- $\mu$ F bypass capacitors as close as possible to the  $V_{CC}$ -pins of transceiver, UART, and controller ICs on the board.
- Use at least two vias for  $V_{CC}$  and ground connections of bypass capacitors and protection devices to minimize effective via-inductance.
- Use 1-k $\Omega$  to 10-k $\Omega$  pullup and pulldown resistors for enable lines to limit noise currents in these lines during transient events.
- Insert pulse-proof resistors into the A and B bus lines if the TVS clamping voltage is higher than the specified maximum voltage of the transceiver bus pins. These resistors limit the residual clamping current into the transceiver and prevent it from latching up.
- While pure TVS protection is sufficient for surge transients up to 1 kV, higher transients require metal-oxide varistors (MOVs) which reduce the transients to a few hundred volts of clamping voltage, and transient blocking units (TBUs) that limit transient current to less than 1 mA.
- Routing the high-speed traces on the top layer avoids the use of vias (and the introduction of their inductances) and allows for clean interconnects between the isolator and the transmitter and receiver circuits of the data link.

If an additional supply voltage plane or signal layer is needed, add a second power and ground plane system to the stack to keep it symmetrical. This makes the stack mechanically stable and prevents it from warping. Also the power and ground plane of each power system can be placed closer together, thus increasing the high-frequency bypass capacitance significantly.

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#### NOTE

For detailed layout recommendations, see Application Note *Digital Isolator Design Guide*, [SLLA284](#).

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## 12.2 Layout Example

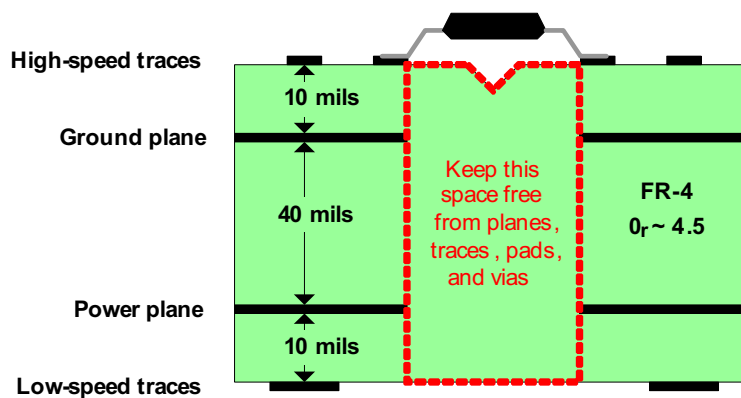


**Figure 35. Recommended Layer Stack**

## 13 Device and Documentation Support

### 13.1 Documentation Support

#### 13.1.1 Related Documentation

For related documentation see the following:

- [SLLA284](#), *Digital Isolator Design Guide*
- [SLLSEA0](#), *Transformer Driver for Isolated Power Supplies*
- [SLLA353](#), *Isolation Glossary*

### 13.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

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### 13.3 Trademarks

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### 13.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 13.5 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## PACKAGING INFORMATION

| Orderable Device | Status<br>(1) | Package Type | Package<br>Drawing | Pins | Package<br>Qty | Eco Plan<br>(2)            | Lead/Ball Finish | MSL Peak Temp<br>(3) | Op Temp (°C) | Top-Side Markings<br>(4) | Samples                 |
|------------------|---------------|--------------|--------------------|------|----------------|----------------------------|------------------|----------------------|--------------|--------------------------|-------------------------|
| ISO1176DW        | ACTIVE        | SOIC         | DW                 | 16   | 40             | Green (RoHS<br>& no Sb/Br) | CU NIPDAU        | Level-2-260C-1 YEAR  | -40 to 85    | ISO1176                  | <a href="#">Samples</a> |
| ISO1176DWG4      | ACTIVE        | SOIC         | DW                 | 16   | 40             | Green (RoHS<br>& no Sb/Br) | CU NIPDAU        | Level-2-260C-1 YEAR  | -40 to 85    | ISO1176                  | <a href="#">Samples</a> |
| ISO1176DWR       | ACTIVE        | SOIC         | DW                 | 16   | 2000           | Green (RoHS<br>& no Sb/Br) | CU NIPDAU        | Level-2-260C-1 YEAR  | -40 to 85    | ISO1176                  | <a href="#">Samples</a> |
| ISO1176DWRG4     | ACTIVE        | SOIC         | DW                 | 16   | 2000           | Green (RoHS<br>& no Sb/Br) | CU NIPDAU        | Level-2-260C-1 YEAR  | -40 to 85    | ISO1176                  | <a href="#">Samples</a> |

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

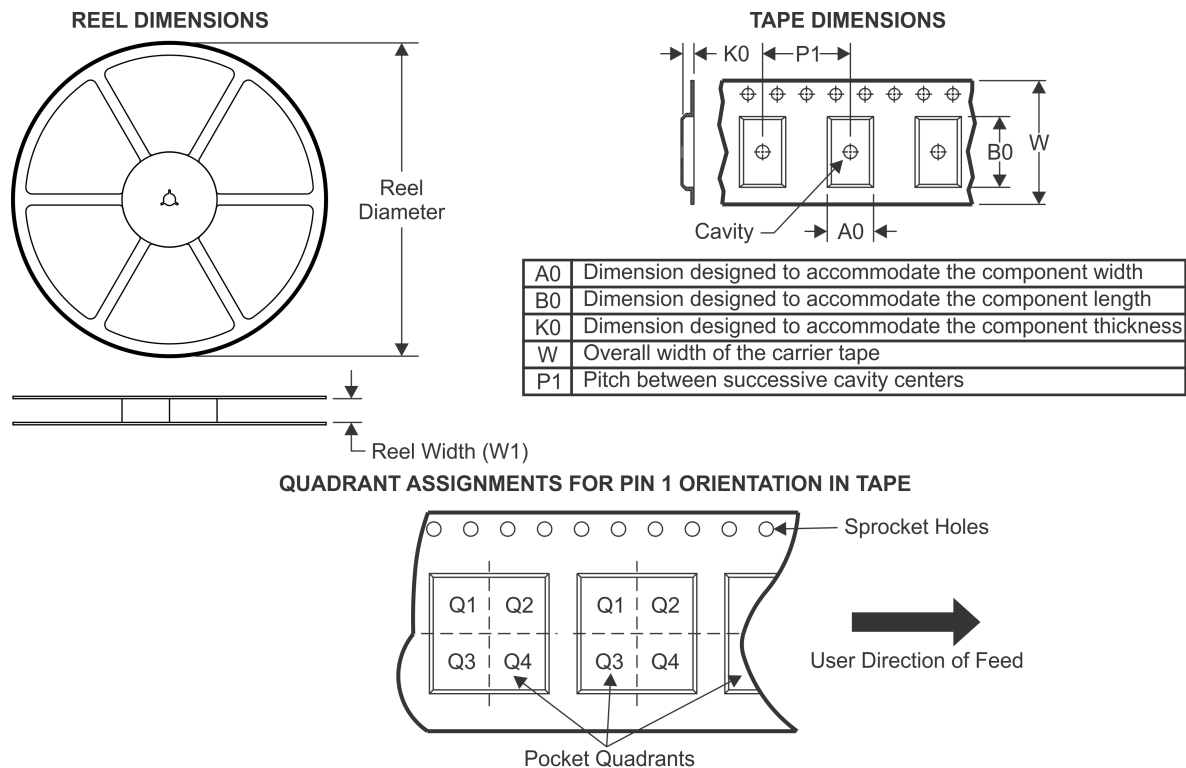
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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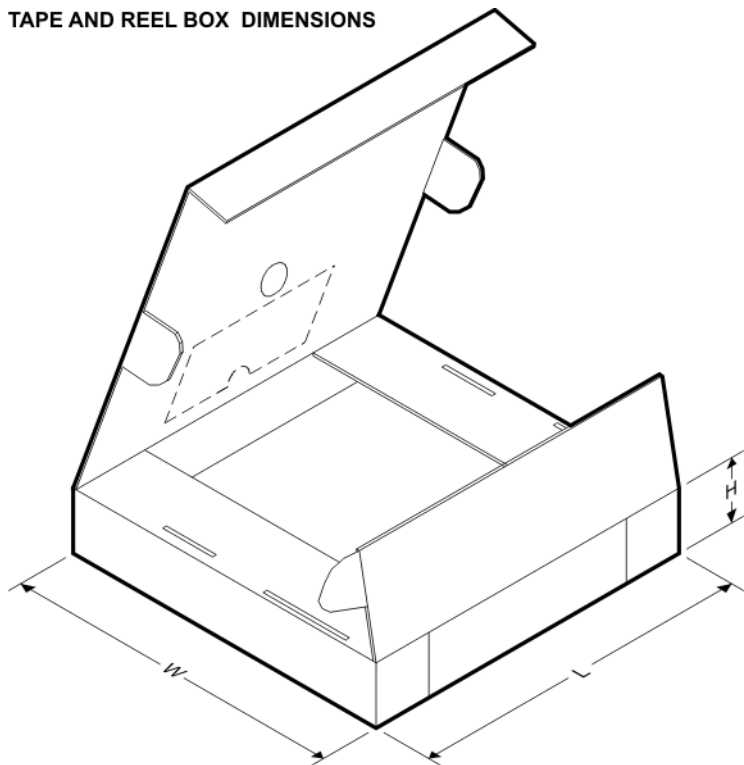


**TAPE AND REEL INFORMATION**


\*All dimensions are nominal

| Device     | Package Type | Package Drawing | Pins | SPQ  | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|------------|--------------|-----------------|------|------|--------------------|--------------------|---------|---------|---------|---------|--------|---------------|
| ISO1176DWR | SOIC         | DW              | 16   | 2000 | 330.0              | 16.4               | 10.75   | 10.7    | 2.7     | 12.0    | 16.0   | Q1            |

## TAPE AND REEL BOX DIMENSIONS

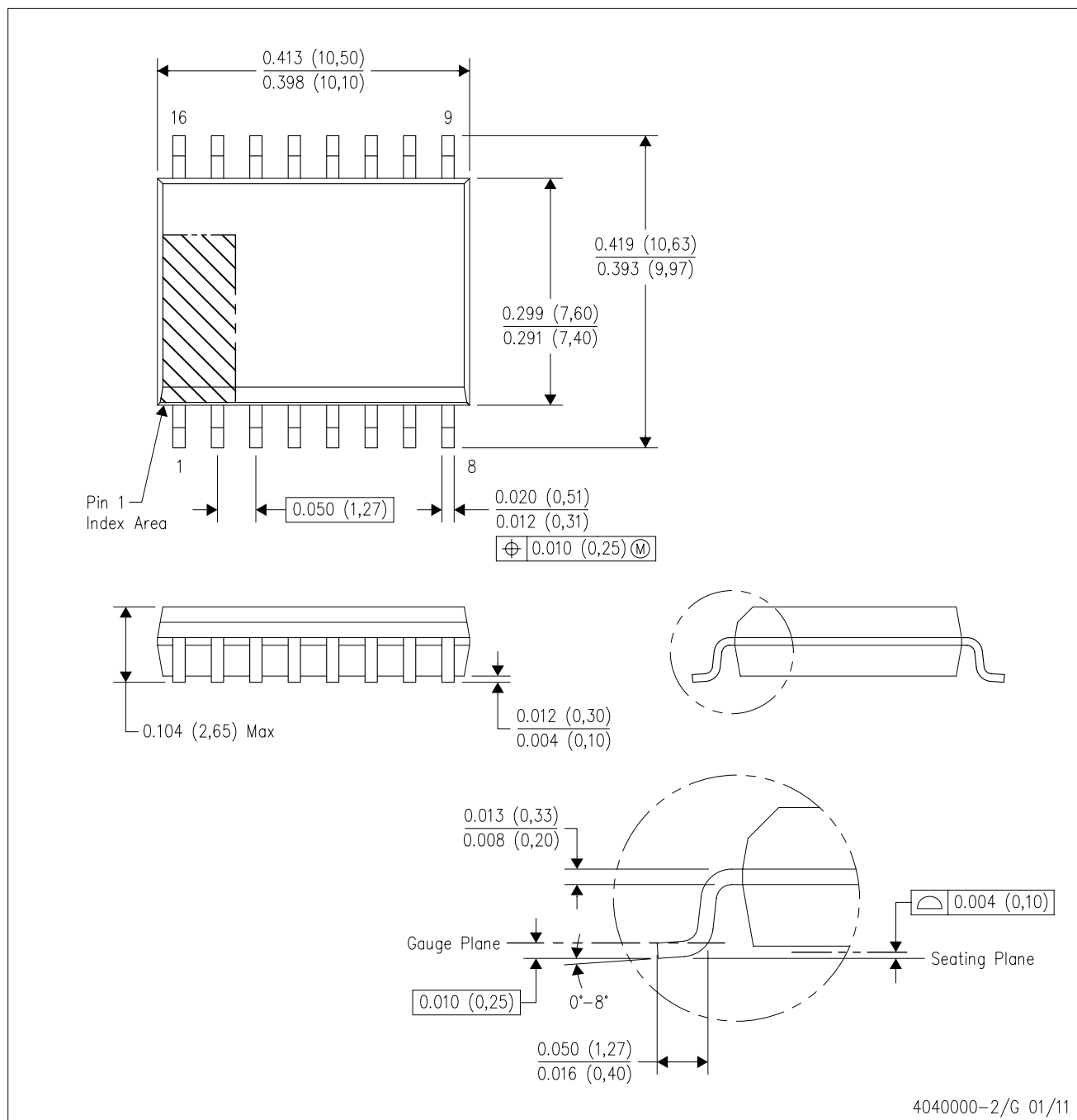


\*All dimensions are nominal

| Device     | Package Type | Package Drawing | Pins | SPQ  | Length (mm) | Width (mm) | Height (mm) |
|------------|--------------|-----------------|------|------|-------------|------------|-------------|
| ISO1176DWR | SOIC         | DW              | 16   | 2000 | 367.0       | 367.0      | 38.0        |

DW (R-PDSO-G16)

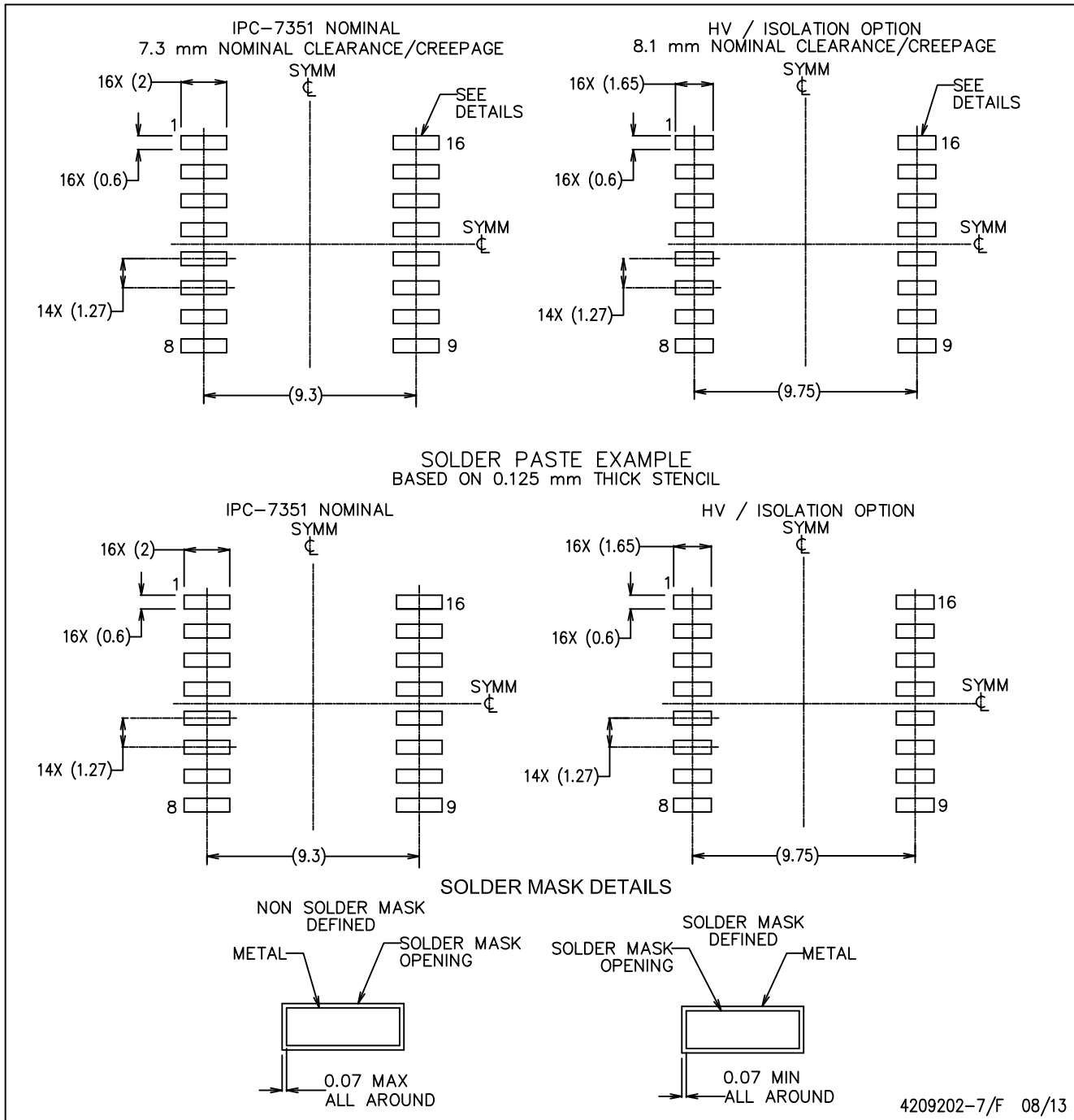
PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.  
 B. This drawing is subject to change without notice.  
 C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).  
 D. Falls within JEDEC MS-013 variation AA.

DW (R-PDSO-G16)

PLASTIC SMALL OUTLINE



4209202-7/F 08/13

- NOTES:
- All linear dimensions are in millimeters.
  - This drawing is subject to change without notice.
  - Refer to IPC7351 for alternate board design.
  - Solder mask tolerances between and around signal pads can vary based on board fabrication site.
  - Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
  - Board assembly site may have different recommendations for stencil design.

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